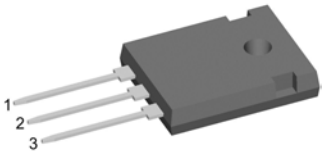
Thyristor

V_{RRM}	=	1600 V
I_{TAV}	=	40 A
V_T	=	1,34 V

Three Quadrants operation: QI - QIII
1~ Triac

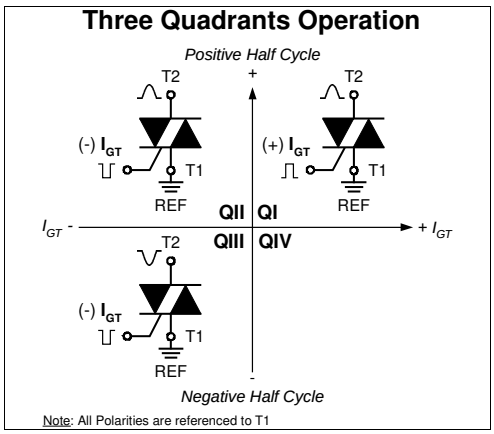
Part number

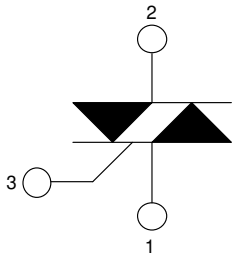
CMA80MT1600NHR



Backside: Isolated

E72873





Features / Advantages:

- Triac for line frequency
- Three Quadrants Operation
  - QI - QIII
- Planar passivated chip
- Long-term stability
  of blocking currents and voltages

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: ISO247

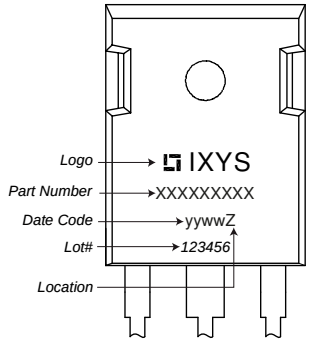
- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Rectifier

Symbol	Definition	Conditions		Ratings min.	typ.	max.	Unit
$V_{RSM/DSM}$	*max. non-repetitive reverse/forward blocking voltage*		T_{VJ} = 25°C			1700	V
$V_{RRM/DRM}$	*max. repetitive reverse/forward blocking voltage*		T_{VJ} = 25°C			1600	V
$I_{R/D}$	*reverse current, drain current*	$V_{R/D}$ = 1600 V	T_{VJ} = 25°C			10	µA
		$V_{R/D}$ = 1600 V	T_{VJ} = 125°C			2	mA
V_T	*forward voltage drop*	I_T = 40 A	T_{VJ} = 25°C			1,36	V
		I_T = 80 A				1,70	V
		I_T = 40 A	T_{VJ} = 125°C			1,34	V
		I_T = 80 A				1,78	V
I_{TAV}	*average forward current*	T_C = 95°C	T_{VJ} = 150°C			40	A
I_{RMS}	*RMS forward current per phase*	180° sine				88	A
V_{T0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 150°C			0,89	V
r_T	*slope resistance* }					11,3	mΩ
R_{thJC}	*thermal resistance junction to case*					0,65	K/W
R_{thCH}	*thermal resistance case to heatsink*				0,25		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			190	W
I_{TSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			380	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			410	A
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			325	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			350	A
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			720	A²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			700	A²s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			530	A²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			510	A²s
C_J	*junction capacitance*	V_R = 400V f = 1 MHz	T_{VJ} = 25°C		14		pF
P_{GM}	*max. gate power dissipation*	t_P = 30 µs	T_C = 150°C			10	W
		t_P = 300 µs				5	W
P_{GAV}	*average gate power dissipation*					0,5	W
$(di/dt)_{cr}$	*critical rate of rise of current*	T_{VJ} = 125°C; f = 50 Hz repetitive, I_T = 90 A				150	A/µs
		t_P = 200 µs; di_G/dt = 0,2 A/µs;					
		I_G = 0,2A; V_D = ⅔ V_{DRM} non-repet., I_T = 40 A				500	A/µs
$(dv/dt)_{cr}$	*critical rate of rise of voltage*	V_D = ⅔ V_{DRM}	T_{VJ} = 125°C			500	V/µs
		R_{GK} = ∞; method 1 (linear voltage rise)					
V_{GT}	*gate trigger voltage*	V_D = 6 V	T_{VJ} = 25°C			1,7	V
			T_{VJ} = -40°C			1,9	V
I_{GT}	*gate trigger current*	V_D = 6 V	T_{VJ} = 25°C			± 70	mA
			T_{VJ} = -40°C			± 90	mA
V_{GD}	*gate non-trigger voltage*	V_D = ⅔ V_{DRM}	T_{VJ} = 125°C			0,2	V
I_{GD}	*gate non-trigger current*					± 1	mA
I_L	*latching current*	t_p = 10 µs	T_{VJ} = 25°C			100	mA
		I_G = 0,2A; di_G/dt = 0,2 A/µs					
I_H	*holding current*	V_D = 6 V R_{GK} = ∞	T_{VJ} = 25°C			70	mA
t_{gd}	*gate controlled delay time*	V_D = ½ V_{DRM}	T_{VJ} = 25°C			2	µs
		I_G = 0,5A; di_G/dt = 0,5 A/µs					
t_q	*turn-off time*	V_R = 100 V; I_T = 40A; V_D = ⅔ V_{DRM}	T_{VJ} =125 °C		150		µs
		di/dt = 10 A/µs; dv/dt = 20 V/µs; t_p = 200 µs					

Package ISO247				Ratings			
Symbol	**Definition**	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
I_{RMS}	*RMS current*	per terminal				70	A
T_{VJ}	*virtual junction temperature*			-40		150	°C
T_{op}	*operation temperature*			-40		125	°C
T_{stg}	*storage temperature*			-40		150	°C
Weight					6		g
M_D	*mounting torque*			0,8		1,2	Nm
F_C	*mounting force with clip*			20		120	N
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	2,7			mm
$d_{Spb/Apb}$			*terminal to backside*	4,1			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; I_{ISOL} ≤ 1 mA	3600			V
		t = 1 minute		3000			V

Product Marking



Part description

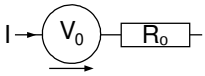
C = Thyristor (SCR)
M = Thyristor
A = (up to 1800V)
80 = Current Rating [A]
MT = 1~ Triac
1600 = Reverse Voltage [V]
N = Three Quadrants operation: QI - QIII
HR = ISO247 (3)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CMA80MT1600NHR	CMA80MT1600NHR	Tube	30	521828

Similar Part	Package	Voltage class
CMA80MT1600NHB	TO-247AD (3)	1600

Equivalent Circuits for Simulation

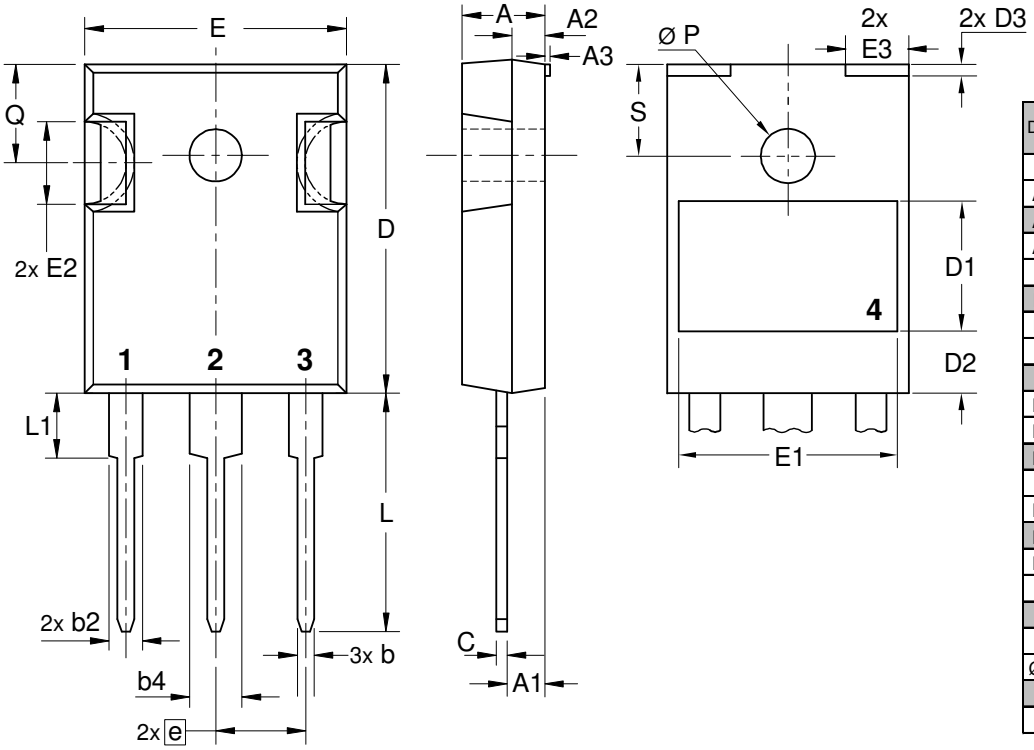
** on die level* T_{VJ} = 150°C



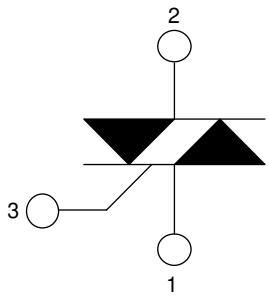
Thyristor

$V_{0\,max}$	*threshold voltage*	0,89	V
$R_{0\,max}$	*slope resistance **	8,8	mΩ

Outlines ISO247



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.70	5.30	0.185	0.209
A1	2.21	2.59	0.087	0.102
A2	1.50	2.49	0.059	0.098
A3	typ. 0.05		typ. 0.002	
b	0.99	1.40	0.039	0.055
b2	1.65	2.39	0.065	0.094
b4	2.59	3.43	0.102	0.135
c	0.38	0.89	0.015	0.035
D	20.79	21.45	0.819	0.844
D1	typ. 8.90		typ. 0.350	
D2	typ. 2.90		typ. 0.114	
D3	typ. 1.00		typ. 0.039	
E	15.49	16.24	0.610	0.639
E1	typ. 13.45		typ. 0.530	
E2	4.31	5.48	0.170	0.216
E3	typ. 4.00		typ. 0.157	
e	5.46 BSC		0.215 BSC	
L	19.80	20.30	0.780	0.799
L1	-	4.49	-	0.177
Ø P	3.55	3.65	0.140	0.144
Q	5.38	6.19	0.212	0.244
S	6.14 BSC		0.242 BSC	



Thyristor

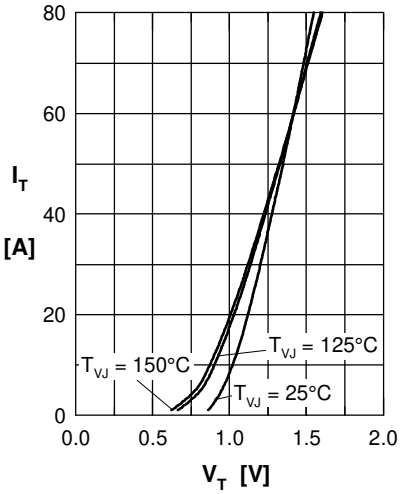


Fig. 1 Forward characteristics

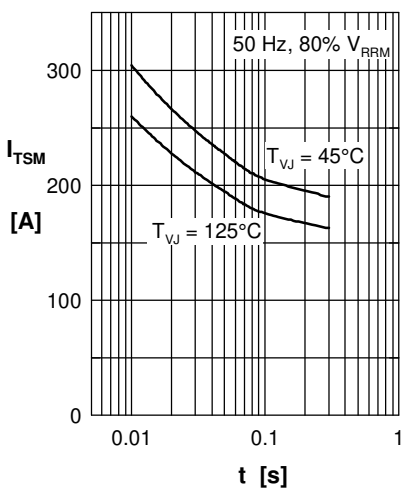


Fig. 2 Surge overload current
I_{TSM}: crest value, t: duration

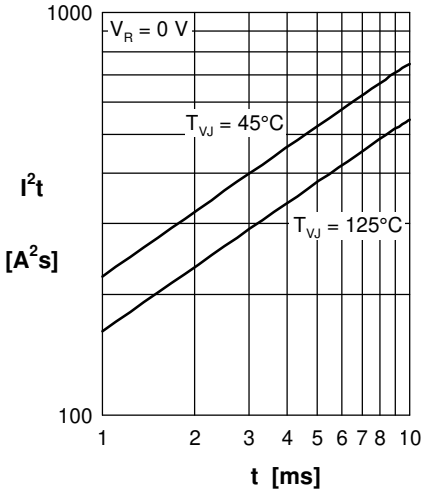


Fig. 3 I^2t versus time (1-10 s)

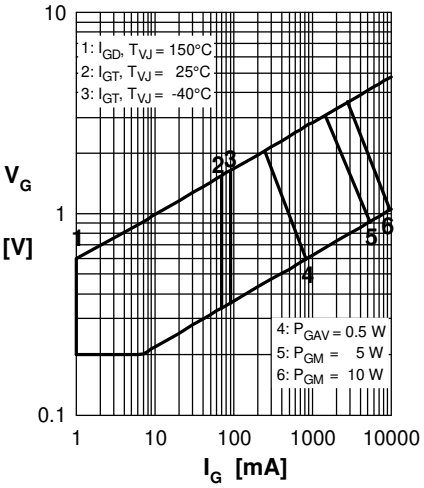


Fig. 4 Gate voltage & gate current

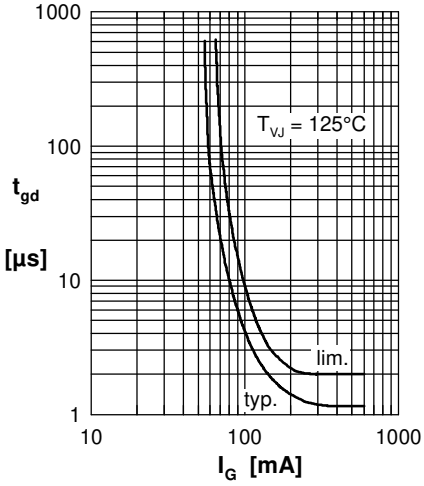


Fig. 5 Gate controlled delay time t_{gd}

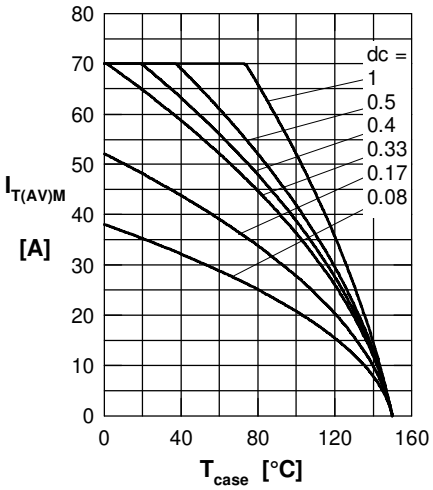


Fig. 6 Max. forward current at case temperature

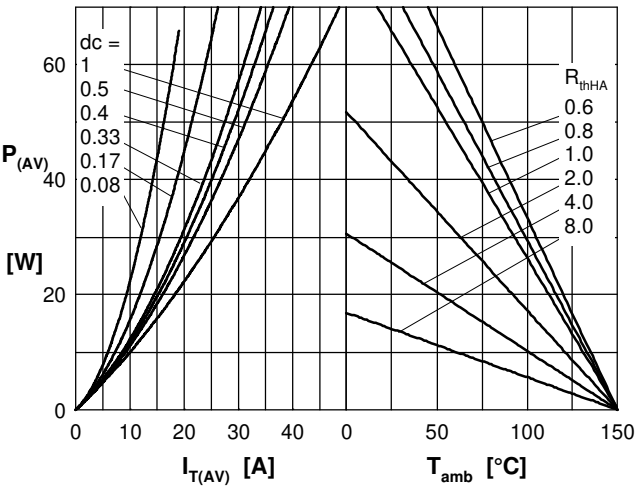
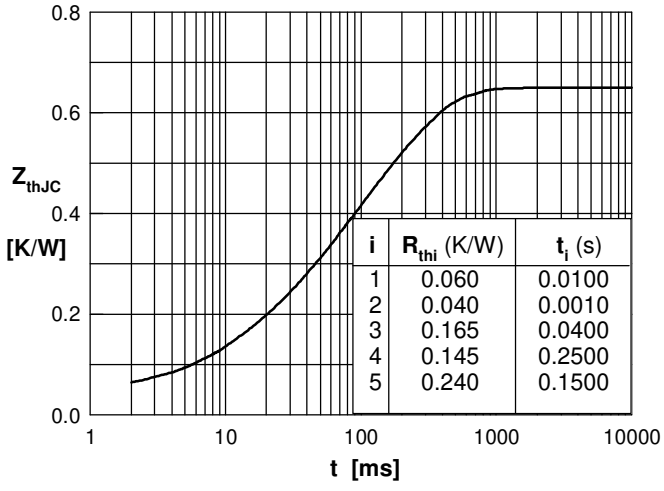


Fig. 7a Power dissipation versus direct output current
Fig. 7b and ambient temperature



i	R_{thi} (K/W)	t_i (s)
1	0.060	0.0100
2	0.040	0.0010
3	0.165	0.0400
4	0.145	0.2500
5	0.240	0.1500

Fig. 8 Transient thermal impedance junction to case